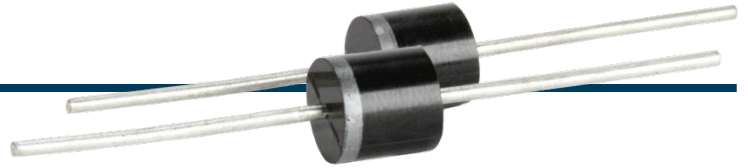




HVW3

3kV, 2000mA, Standard Recovery
Axial Lead Power Diode



Features

- P600 Package
- Molded Plastic Body, ANSI/UL94 V-0 Rated Material

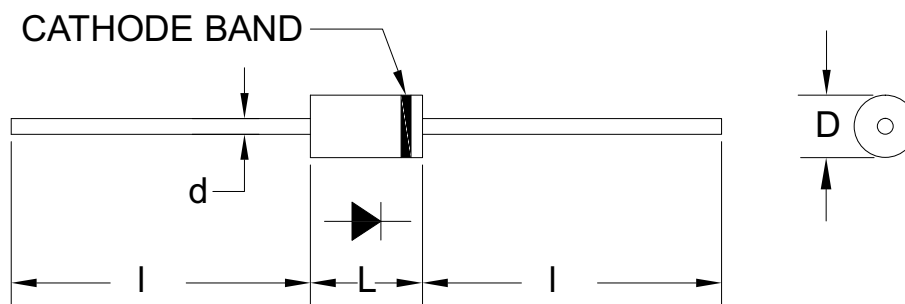
Specifications¹

Part Number	V_{RRM} V	I_{FAVM} mA	V_F V	I_R μ A	I_{FSM} A	L in.	D in.	d in.	l in.
HVW3	3000	2000	3	5	300	0.36	0.36	0.05	0.94

Temperature °C	
Operating Temperature	-55 to 125
Storage Temperature	-55 to 175
Maximum Junction Temperature	125

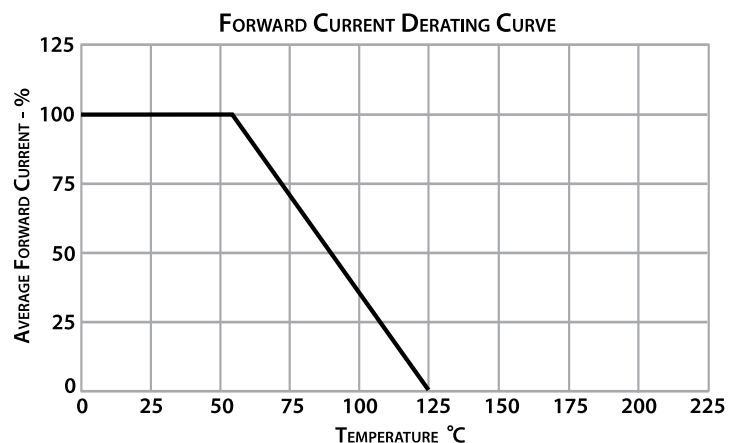
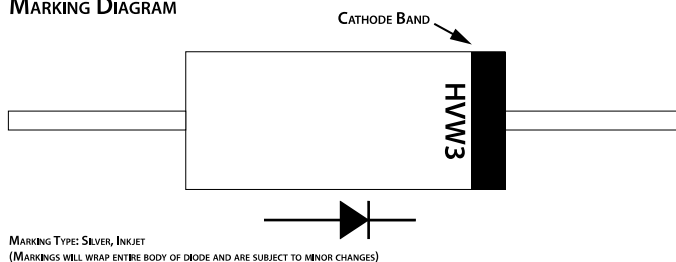
¹125°C ambient temperature unless stated otherwise.

Drawings



Dimensions in inches, tolerances ± 0.020 except as noted

MARKING DIAGRAM





Specification Definitions

Specifications		Conditions
V_{RRM}	Maximum Repetitive Reverse Voltage	-
I_{FAVM}	Maximum Average Forward Current	At T _A = 55°C
V_F	Maximum Forward Voltage Drop	At I _{FAVM}
I_R	Maximum Leakage Current	At V _{RRM}
I_{FSM}	Maximum Surge Current	At 8.3mS, Single Half Sine

Note: Specifications subject to change without notice. Photo is representation only.





HVRW SERIES

1 to 4kV, 1.0 to 2.5A, 150nS
Axial Lead Power Diodes



Features

- Fast Reverse Recovery Time
- 0.38" x 0.32" Package
- Molded Plastic Body, ANSI/UL94 V-0 Rated Material

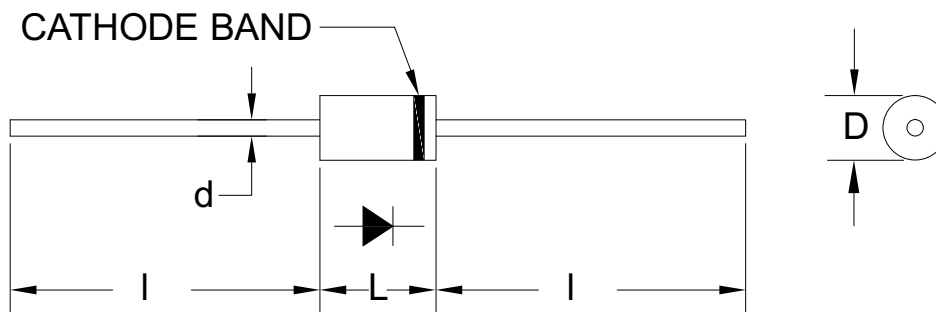
Specifications¹

Part Number	V _{RRM} V	I _{FAVM} mA	V _F V	I _R μA	I _{FSM} A	C _J pF	T _{RR} nS	L in.	D in.	d in.	l in.
HVRW1	1000	2500	2	10	200	105	150	0.38	0.32	0.05	0.94
HVRW2	2000	1500	4	10	200	52	150	0.38	0.32	0.05	0.94
HVRW3	3000	1500	5	10	200	35	150	0.38	0.32	0.05	0.94
HVRW4	4000	1000	6	10	200	27	150	0.38	0.32	0.05	0.94

Temperature °C	
Operating Temperature	-55 to 150
Storage Temperature	-55 to 175
Maximum Junction Temperature	150

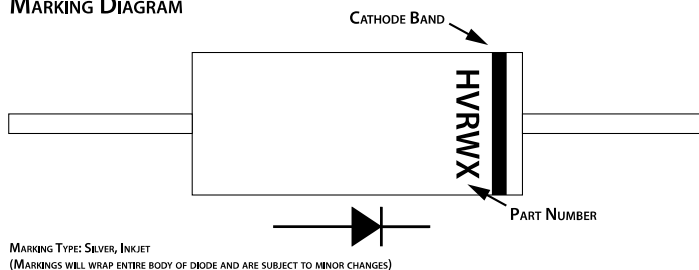
¹125°C ambient temperature unless stated otherwise.

Drawings

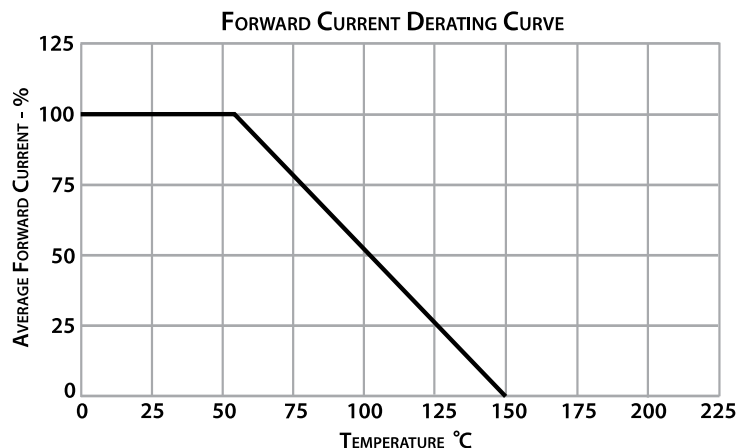


Dimensions in inches, tolerances ±0.020 except as noted

MARKING DIAGRAM



MARKING TYPE: SILVER, INKJET
(MARKINGS WILL WRAP ENTIRE BODY OF DIODE AND ARE SUBJECT TO MINOR CHANGES)





Specification Definitions

Specifications		Conditions
V_{RRM}	Maximum Repetitive Reverse Voltage	-
I_{FAVM}	Maximum Average Forward Current	At T _A = 55°C
V_F	Maximum Forward Voltage Drop	At I _{FAVM}
I_R	Maximum Leakage Current	At V _{RRM}
I_{FSM}	Maximum Surge Current	At 8.3mS, Single Half Sine
C_J	Typical Junction Capacitance	At V _R = 0VDC, f = 1MHz
T_{RR}	Maximum Reverse Recovery Time	I _F = 500mA; I _R = -1000mA; I _{RR} = -250mA

Note: Specifications subject to change without notice. Photo is representation only.

